

ABSTRACT

In order to obtain compound semiconductor devices which has uniform and stable performance on a wafer and a long life span, the present invention
5 provides an indium phosphide substrate and a method for manufacturing the same in which the dislocation density is low and there is excellent uniformity of dopant concentration on the wafer as well as in the depth direction.

In order to have the direction of growth of the crystal in the $\langle 100 \rangle$ orientation, a seed crystal having a specified cross-sectional area ratio with the
10 crystal body is placed at the lower end of a growth container. The growth container housing the seed crystal, indium phosphide raw material, dopant, and boron oxide is placed in a crystal growth chamber. The temperature is raised to at or above the melting point of indium phosphide. After melting the boron oxide, indium phosphide raw material, and dopant, the temperature of
15 the growth container is lowered in order to obtain an indium phosphide monocrystal having a low dislocation density and a uniform dopant concentration on the wafer as well as in the depth direction.